



E. Compound Semiconductors 분과

2019년 2월 15일(금), 11:00-12:15

Room H (루비1+2, 5층)

[FH2-E] Compound Process Technology

좌장: 김정진 박사(ETRI)

<p><b>FH2-E-1</b> 11:00-11:30</p>	<p>[초청] Performance of 0.4 um Gate GaN HEMT Devices Fabricated on 4" SiC Substrates in a Production Environment Sangmin Lee<sup>1</sup>, Byoungchul Jun<sup>1</sup>, Chulsoon Choi<sup>1</sup>, Seokgyu Choi<sup>1</sup>, Min Han<sup>1</sup>, Hogeun Lee<sup>1</sup>, Myoungkeun Song<sup>1</sup>, Jihun Kwon<sup>1</sup>, Myungsoo Park<sup>1</sup>, Sungwon Lee<sup>1</sup>, Yongjae Kim<sup>1</sup>, Hyeyoung Jung<sup>1</sup>, Hankyul Ji<sup>1</sup>, Junho Choi<sup>2</sup>, and Hosang Kwon<sup>2</sup> <sup>1</sup>Advanced Device R&amp;D Center, Wavice Inc., <sup>2</sup>Agency for Defense Development</p>
<p><b>FH2-E-2</b> 11:30-11:45</p>	<p>Stripping of High Dose Ion Implanted Photoresist on Patterned GaAs Eunseok Oh and Sangwoo Lim Department of Chemical and Biomolecular Engineering, Yonsei University</p>
<p><b>FH2-E-3</b> 11:45-12:00</p>	<p>Fabrication of MOCVD-grown InGaAs Tunnel Field Effect Transistor Minwoo Kong<sup>1,2</sup>, Sukeun Eom<sup>1,2</sup>, Kwangwook Park<sup>3</sup>, Chansoo Shin<sup>3</sup>, and Kwangseok Seo<sup>1,2</sup> <sup>1</sup>Department of Electrical and Computer Engineering, Seoul National University, <sup>2</sup>Inter-university Semiconductor Research Center, Seoul National University, <sup>3</sup>KANC</p>
<p><b>FH2-E-4</b> 12:00-12:15</p>	<p>GaN Template Mass Production System Chung-Seok Oh, Se-Hun Yeon, and Min-Seo Park R&amp;D Center, Han Sung S-Tec Co., Ltd</p>